# MW39580AE

# Diagonal 11 mm (type-2/3) IT CCD Area Image Sensor

# Overview

The MW39580AE is a type-2/3 2.2M-pixel CCD solid state image sensor.

This device uses photodiodes in the opto-electric conversion section and CCDs for signal read-out. The electronic shutter function allows for an exposure time of 1/10000 seconds. Further, it features high sensitivity, low noise, broad dynamic range and low smear level.

The device has a total of 2182860 pixels (2010 horizontal  $\times$  1086 vertical) and provides stable and clear images with a resolution of 1100 horizontal and 730 vertical TV lines.

Part Number	CCD size	System	Color or B/W
MW39580AE	11 mm (type-2/3)	HDTV	B/W

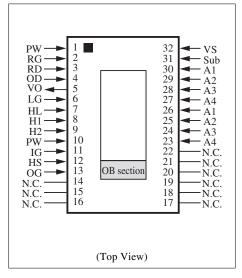
### Features

- Effective pixel number: 1936 (horizontal) × 1086 (vertical)
- High sensitivity
- High resolution
- Low smear level
- · Continuously variable-speed electronic shutter function

## Applications

- · Broadcasting and professional use camera
- Front-edge surveillance camera

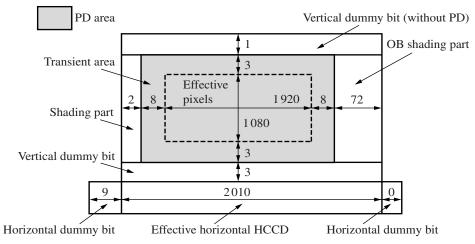
#### Pin Assignments



# Device Configuration

Parameter	Value	Unit
Horizontal drive frequency	$f_{CK} = 2200 \ f_{H} = 74.25$	MHz
Total pixel number	2010 (H) × 1086 (V)	Pixel
Effective pixel number (including transient ones)	1936 (H) × 1086 (V)	Pixel
Effective pixel number	1920 (H) × 1080 (V)	Pixel
Pixel size	5.0 (H) × 5.0 (V)	μm <sup>2</sup>
Effective image sensor size	9.6 (H) × 5.4 (V)	mm <sup>2</sup>
Aspect ratio	16 : 9	H : V
Aspect ratio error	0.0	%

#### • Element Construction



Note) The horizontal dummy bit is based on 2 gates = 1 unit.

# Pin Descriptions

Pin No.	Symbol	Description	Pin No.	Symbol	Description
1	PW	P-well	13	OG	Output gate
2	RG	Reset gate	14	N.C.	Non Connection
3	RD	Reset drain	15	N.C.	Non Connection
4	OD	Output drain	16	N.C.	Non Connection
5	VO	Video output	17	N.C.	Non Connection
6	LG	Output load transistor gate	18	N.C.	Non Connection
7	HL	Horizontal CCD final gate	19	N.C.	Non Connection
8	H1	Horizontal CCD 1	20	N.C.	Non Connection
9	H2	Horizontal CCD 2	21	N.C.	Non Connection
10	PW	P-well	22	N.C.	Non Connection
11	IG	Horizontal input gate	23	A4	Vertical CCD gate 4
12	HS	Horizontal input source	24	A3	Vertical CCD gate 3

# ■ Pin Descriptions (continued)

Pin No.	Symbol	Description	Pin No.	Symbol	Description
25	A2	Vertical CCD gate 2	29	A2	Vertical CCD gate 2
26	A1	Vertical CCD gate 1	30	A1	Vertical CCD gate 1
27	A4	Vertical CCD gate 4	31	Sub	Substrate
28	A3	Vertical CCD gate 3	32	VS	Vertical input source

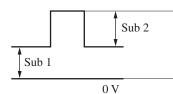
# ■ Absolute Maximum Ratings and Operating Conditions

Pin No.	Parameter		Absolute maximum rating		Operating condition			Unit
PIN NO.			Lower limit	Upper limit	Min	Тур	Max	
1	PW		Referenc	e voltage		0.0		V
2	RG	Amplitude	0	9.0	4.7	5.0	5.3	V
		Low	0		5.5	adj.	7.0	V
3	RD	1	0	18	15.7	16.0	16.3	V
4	OD		0	18	15.7	16.0	16.3	V
5	VO		_			_		V
6	LG		0	6	2.7	3.0	3.3	V
7	$\phi_{HL}$	High	_	10	2.7	3.0	3.3	V
		Low	0		0.0	00	0.3	V
8	$\phi_{H1}$	High	_	10	2.7	3.0	3.3	V
		Low	0		0.0	0.0	0.3	V
9	$\phi_{H2}$	High	_	10	2.7	3.0	3.3	V
		Low	0		0.0	0.0	0.3	V
10	PW	1	Referenc	e voltage		0.0		V
11	IG		0	5		0.0		V
12	HS		0	18	15.7	16.0	16.3	V
13	OG		0	5	0.0	0.0	0.3	V
14	N.C.		_			_		_
15	N.C.		_		_	_		_
16	N.C.		_	_	_	_		_
17	N.C.		_			_		
18	N.C.		_			_		_
19	N.C.		_	_	_	_		_
20	N.C.		—			—		—
21	N.C.		_			_		_
22	N.C.		—			_		_
23	$\phi_{A4}$	Middle	_	18	0.7	1.0	1.3	V
		Low	-12		-9.3	-9.0	-8.7	v

	Dam		Absolute ma	ximum rating	Operating condition			Linit
Pin No.	Para	Parameter		Upper limit	Min	Тур	Max	- Unit
24	φ <sub>A3</sub>	High	_	18	15.7	16.0	16.3	V
		Middle	_	18	- 0.3	0.0	0.3	V
		Low	-12		-9.3	-9.0	-8.7	V
25	φ <sub>A2</sub>	Middle	_	18	0.7	1.0	1.3	V
		Low	-12		-9.3	-9.0	-8.7	V
26	φ <sub>A1</sub>	High	_	18	15.7	16.0	16.3	V
		Middle	_	18	- 0.3	0.0	0.3	V
		Low	-12		-9.3	-9.0	-8.7	V
27	$\phi_{A4}$	Middle	_	18	0.7	1.0	1.3	V
		Low	-12		-9.3	-9.0	-8.7	V
28 \$\phi_{A3}\$	<b>ф</b> <sub>А3</sub>	High	_	18	15.7	16.0	16.3	V
		Middle	_	18	- 0.3	0.0	0.3	V
	Low	-12		-9.3	-9.0	-8.7	V	
29	29	Middle	_	18	0.7	1.0	1.3	V
		Low	-12		-9.3	-9.0	-8.7	V
30	30 \$\phi_{A1}\$	High	_	18	15.7	16.0	16.3	V
		Middle	_	18	- 0.3	0.0	0.3	V
		Low	-12		-9.3	-9.0	-8.7	V
31	Sub *1	1	0	40 *2	3.0	adj.	14.0	V
		2	0	40	24.0	25.0	26.0	V
32	VS		0	18	15.7	16.0	16.3	V
Operati	ng temperatu	ıre	-10	60		25		°C
Storage	e temperature	;	-30	70	_	_		°C

# Absolute Maximum Ratings and Operating Conditions (continued)

Note) \*1: Sub pulse at the electronic shutter



\*2: Upper limit of Sub maximum rating:

Sub 1 + Sub 2  $\leq$  40 V

### Image Sensor Characteristics $T_a = 25^{\circ}C$

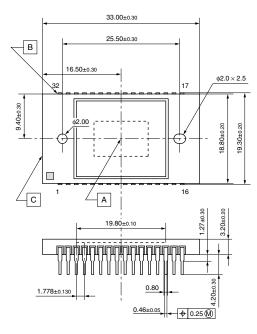
Parameter		Conditions	Min	Тур	Max	Unit	Remarks	
Saturation output		F value adjust	600	750	_	mV	at CCD out	
Standard output		J chart, Standard light intensity	100	120		mV	at CCD out	
Image lag		1/10 light intensity		0		%	Able to be swept out directly to substrate	
Vertical smear		1/10 V	—	-102	-96	dB	Ratio to standard output	
Transfer efficiency H F11 + 1/32ND			Resolution should not be reduced.					
	V							
Electronic shutter		Specified driving	No abnormality within 1/100 to 1/2000 seconds					

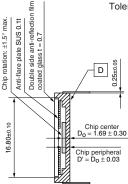
Note) 1. The substrate voltage (Sub 1) should be adjusted to the minimum voltage that would not cause blooming, overflow and injection at image sensor of light input of 1 600 times the standard light intensity.

2. The standard light intensity is the one when the exposure is done at an aperture of F/11 using a light source of 2856K and 920 nt and placing a color temperature conversion filter LB-40 (HOYA) and an IR cutting filter CAW-500S (t = 2.5 mm) in the light path.

### Package Dimensions (unit: mm)

• WDIP032-G-0750C (Lead-free package)





Tolerance:  $\pm 0.20$  unless otherwise specified

- 1. The package center must meet the center of the effective pixel area. A is the center of the effective pixel area.
- The reference of a vertical direction(V) is the side B. The reference of a horizontal direction(H) is the side C. The reference of a height direction is the package bottom D.
- 3. The rotation precision of the effective pixel area: maximum  $\pm 1.5^{\circ}$
- 4. The distance from the package bottom D to the effective pixel area : 1.69 mm  $\pm$  0.3 mm
- 5. The tilt of the effective pixel area toward the package bottom D : D' =  $D_0 \pm max$ . 0.03 mm
- 6. The thickness of the seal glass: 0.7 mm, and the refractive index :  $1.50\,$

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